

Daniel Alquier

List of Publications by Year in descending order

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158
papers

1,581
citations

394421

19
h-index

454955

30
g-index

159
all docs

159
docs citations

159
times ranked

1546
citing authors

#	ARTICLE	IF	CITATIONS
1	Assessing the electrical activity of individual ZnO nanowires thermally annealed in air. <i>Nanoscale Advances</i> , 2022, 4, 1125-1135.	4.6	3
2	Integrating porous silicon layer backing to capacitive micromachined ultrasonic transducers (CMUT)-based linear arrays for acoustic Lamb wave attenuation. <i>Journal of Applied Physics</i> , 2022, 131, 105107.	2.5	0
3	Fabrication of Piezoelectric ZnO Nanowires Energy Harvester on Flexible Substrate Coated with Various Seed Layer Structures. <i>Nanomaterials</i> , 2021, 11, 1433.	4.1	15
4	Broad bandwidth air-coupled micromachined ultrasonic transducers for gas sensing. <i>Ultrasonics</i> , 2021, 114, 106410.	3.9	15
5	Influence of topology and diode characteristics of AC-DC converters for low power piezoelectric energy harvesting. <i>Sensors and Actuators A: Physical</i> , 2021, 330, 112901.	4.1	4
6	Editorial for the Special Issue on SiC Based Miniaturized Devices. <i>Micromachines</i> , 2020, 11, 405.	2.9	0
7	A Comparative Study on the Effects of Au, ZnO and AZO Seed Layers on the Performance of ZnO Nanowire-Based Piezoelectric Nanogenerators. <i>Materials</i> , 2019, 12, 2511.	2.9	12
8	Effect of the excitation waveform on the average power and peak power delivered by a piezoelectric generator. <i>Mechanical Systems and Signal Processing</i> , 2019, 133, 106278.	8.0	3
9	Stability evaluation of ZnO nanosheet based source-gated transistors. <i>Scientific Reports</i> , 2019, 9, 2979.	3.3	25
10	Deposition Time and Annealing Effects of ZnO Seed Layer on Enhancing Vertical Alignment of Piezoelectric ZnO Nanowires. <i>Chemosensors</i> , 2019, 7, 7.	3.6	21
11	High Frequency Gas Detection With an Uncoated CMUT Array by Impedance Resonant Frequency Measurement. , 2019, , .		0
12	Effects of Aluminum Incorporation on the Young's Modulus of 3C-SiC Epilayers. <i>Materials Science Forum</i> , 2019, 963, 305-308.	0.3	1
13	Investigation of the Young's Modulus and the Residual Stress of 4H-SiC Circular Membranes on 4H-SiC Substrates. <i>Micromachines</i> , 2019, 10, 801.	2.9	12
14	Flexible CMUT for Vibrating Mesh Nebulize. , 2019, , .		1
15	Challenges of low-temperature synthesized ZnO nanostructures and their integration into nano-systems. <i>Materials Science in Semiconductor Processing</i> , 2019, 91, 404-408.	4.0	11
16	Performance Evaluation of CMUT-Based Ultrasonic Transformers for Galvanic Isolation. <i>IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control</i> , 2018, 65, 617-629.	3.0	13
17	Double buffer circuit for the characterization of piezoelectric nanogenerators based on ZnO nanowires. <i>Applied Physics Letters</i> , 2018, 112, .	3.3	21
18	Organic/Inorganic Hybrid Stretchable Piezoelectric Nanogenerators for Self-Powered Wearable Electronics. <i>Advanced Materials Technologies</i> , 2018, 3, 1700249.	5.8	107

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19	CMUT-Based Single Element Transducer Applied to 1D Transient Ultrasound Elastography. , 2018, , .		1
20	Photoluminescence Study of the Influence of Additive Ammonium Hydroxide in Hydrothermally Grown ZnO Nanowires. Nanoscale Research Letters, 2018, 13, 249.	5.7	14
21	Zinc oxide nanowire-parylene nanocomposite based stretchable piezoelectric nanogenerators for self-powered wearable electronics. Journal of Physics: Conference Series, 2018, 1052, 012028.	0.4	6
22	CMUT Based Air Coupled Transducers for Gas-Mixture Analysis. , 2018, , .		4
23	A simple non-recessed and Au-free high quality Ohmic contacts on AlGaIn/GaN: The case of Ti/Al alloy. Materials Science in Semiconductor Processing, 2018, 78, 107-110.	4.0	17
24	Turning the undesired voids in silicon into a tool: In-situ fabrication of free-standing 3C-SiC membranes. Applied Physics Letters, 2017, 110, 081602.	3.3	5
25	An editorial on the recent advances in high and low temperature electronics. Semiconductor Science and Technology, 2017, 32, 080201.	2.0	2
26	Impact of rapid thermal annealing on Mg-implanted GaN with a SiO ₂ /AlN cap-layer. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1600438.	1.8	5
27	Flexible Organic/Inorganic Hybrid Field-Effect Transistors with High Performance and Operational Stability. ACS Applied Materials & Interfaces, 2017, 9, 573-584.	8.0	32
28	Spring E-MRS 2016 Symposium L "Wide bandgap materials for electron devices". Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1770124.	1.8	0
29	A facile hydrothermal approach for the density tunable growth of ZnO nanowires and their electrical characterizations. Scientific Reports, 2017, 7, 15187.	3.3	59
30	A detailed study of AlN and GaN grown on silicon-on-porous silicon substrate. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1600450.	1.8	5
31	Laser irradiation influence on Si/3C-SiC/Si heterostructures for subsequent 3C-SiC membrane elaboration. MRS Advances, 2016, 1, 3649-3654.	0.9	2
32	DLTS analysis of high resistive edge termination technique-induced defects in GaN-based Schottky barrier diodes. Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 2364-2370.	1.8	7
33	Realization of minimum number of rotational domains in heteroepitaxied Si(110) on 3C-SiC(001). Applied Physics Letters, 2016, 108, 011608.	3.3	4
34	Optimized plasma-polymerized fluoropolymer mask for local porous silicon formation. Journal of Applied Physics, 2016, 119, 213301.	2.5	4
35	On the interplay between Si(110) epilayer atomic roughness and subsequent 3C-SiC growth direction. Journal of Applied Physics, 2016, 120, .	2.5	3
36	Porous silicon as backing material for Capacitive Micromachined Ultrasonic Transducers. , 2016, , .		1

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37	Representation of CMUT-based isolation transformer by means of an electrical two-port network. , 2016, , .		1
38	Temperature dependence of charge transport in zinc oxide nanosheet source-gated transistors. Thin Solid Films, 2016, 617, 114-119.	1.8	5
39	Measurement of Spurious Voltages in ZnO Piezoelectric Nanogenerators. Journal of Microelectromechanical Systems, 2016, 25, 533-541.	2.5	18
40	Etching optimization of post aluminum-silicon thermomigration process residues. Microelectronic Engineering, 2016, 149, 97-105.	2.4	7
41	Gallium nitride surface protection during RTA annealing with a GaO _x N _y cap-layer. Semiconductor Science and Technology, 2016, 31, 045008.	2.0	4
42	Universal model for defect-related visible luminescence in ZnO nanorods. RSC Advances, 2016, 6, 73170-73175.	3.6	16
43	Novel 3C-SiC Microstructure for MEMS Applications. Materials Science Forum, 2016, 858, 723-728.	0.3	1
44	Low temperature capacitive micromachined ultrasonic transducers (cMUTs) on glass substrate. Journal of Micromechanics and Microengineering, 2016, 26, 115023.	2.6	2
45	Single-crystalline ZnO sheet Source-Gated Transistors. Scientific Reports, 2016, 6, 19232.	3.3	33
46	Source-gating effect in hydrothermally grown ZnO nanowire transistors. Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 2438-2445.	1.8	7
47	Porosity and thickness characterization of porous Si and oxidized porous Si layers " An ultraviolet-visible mid infrared ellipsometry study. Microporous and Mesoporous Materials, 2016, 227, 112-120.	4.4	16
48	Two-dimensional dopant profiling of gallium nitride p-n junctions by scanning capacitance microscopy. Nuclear Instruments & Methods in Physics Research B, 2016, 372, 67-71.	1.4	3
49	Modeling and Characterization of cMUT-based Devices Applied to Galvanic Isolation. Physics Procedia, 2015, 70, 987-991.	1.2	2
50	Fabrication of ZnO Nanowire Based Piezoelectric Generators and Related Structures. Physics Procedia, 2015, 70, 858-862.	1.2	43
51	Zinc oxide sheet field-effect transistors. Applied Physics Letters, 2015, 107, 033105.	3.3	19
52	cMUT technology applied to galvanic isolation: Theory and experiments. , 2015, , .		2
53	Fabrication and Characterization of ZnO Nanowire-based Piezoelectric Nanogenerators for Low Frequency Mechanical Energy Harvesting. Physics Procedia, 2015, 70, 909-913.	1.2	27
54	Fabrication of high performance field-effect transistors and practical Schottky contacts using hydrothermal ZnO nanowires. Nanotechnology, 2015, 26, 355704.	2.6	25

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55	Toward high-quality 3C-SiC membrane on a 3C-SiC pseudo-substrate. <i>Materials Letters</i> , 2015, 160, 28-30.	2.6	6
56	Fabrication of field-effect transistors and functional nanogenerators using hydrothermally grown ZnO nanowires. <i>RSC Advances</i> , 2015, 5, 69925-69931.	3.6	29
57	Surface state of GaN after rapid-thermal-annealing using AlN cap-layer. <i>Applied Surface Science</i> , 2015, 355, 1044-1050.	6.1	9
58	Direct insight into grains formation in Si layers grown on 3C-SiC by chemical vapor deposition. <i>Acta Materialia</i> , 2015, 98, 336-342.	7.9	13
59	Electrothermally driven high-frequency piezoresistive SiC cantilevers for dynamic atomic force microscopy. <i>Journal of Applied Physics</i> , 2014, 116, .	2.5	15
60	Controlled growth of 1D and 2D ZnO nanostructures on 4H-SiC using Au catalyst. <i>Nanoscale Research Letters</i> , 2014, 9, 379.	5.7	25
61	Characterization of in-depth cavity distribution after thermal annealing of helium-implanted silicon and gallium nitride. <i>Thin Solid Films</i> , 2014, 571, 567-572.	1.8	1
62	Progresses in cMUT device fabrication using low temperature processes. <i>Journal of Micromechanics and Microengineering</i> , 2014, 24, 045020.	2.6	11
63	Original 3C-SiC micro-structure on a 3C-SiC pseudo-substrate. <i>Microelectronic Engineering</i> , 2013, 105, 65-67.	2.4	15
64	Delta-Doping of Epitaxial GaN Layers on Large Diameter Si(111) Substrates. <i>Applied Physics Express</i> , 2012, 5, 025504.	2.4	9
65	Fabrication Issues of 4H-SiC Static Induction Transistors. <i>Materials Science Forum</i> , 2012, 717-720, 1049-1052.	0.3	6
66	Investigations on the Origin of the Ohmic Behavior for Ti/Al Based Contacts on n-Type GaN. <i>Materials Science Forum</i> , 2012, 711, 208-212.	0.3	3
67	Ti Thickness Influence for Ti/Ni Ohmic Contacts on N-Type 3C-SiC. <i>Materials Science Forum</i> , 2012, 711, 179-183.	0.3	5
68	Detailed Experimental Study of Mean and Gradient Stresses in Thin 3C-SiC Films Performed Using Micromachined Cantilevers. <i>Materials Science Forum</i> , 2012, 711, 84-88.	0.3	1
69	Design, characterization and test of a multi-transmitters, multi-receivers probe based on cMUTs for cortical bone evaluation. , 2012, , .		0
70	Recent Progresses in GaN Power Rectifier. <i>Japanese Journal of Applied Physics</i> , 2012, 51, 01AG08.	1.5	7
71	Experimental observation and analytical model of the stress gradient inversion in 3C-SiC layers on silicon. <i>Journal of Applied Physics</i> , 2012, 111, .	2.5	21
72	TiAl Ohmic contact on GaN, <i>in situ</i> high or low doped or Si implanted, epitaxially grown on sapphire or silicon. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2012, 209, 1059-1066.	1.8	7

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73	A new approach for AFM cantilever elaboration with 3C-SiC. <i>Materials Letters</i> , 2012, 77, 54-56.	2.6	15
74	Si implanted reactivation in GaN grown on sapphire using AlN and oxide cap layers. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2012, 272, 137-140.	1.4	12
75	Carrier profiling in Si-implanted gallium nitride by Scanning Capacitance Microscopy. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2012, 275, 37-40.	1.4	5
76	Recent Progresses in GaN Power Rectifier. <i>Japanese Journal of Applied Physics</i> , 2012, 51, 01AG08.	1.5	8
77	Structural and electrical characterizations of n-type implanted layers and ohmic contacts on 3C-SiC. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2011, 269, 2020-2025.	1.4	14
78	Low temperature (down to 450 Å°C) annealed TiAl contacts on n-type gallium nitride characterized by differential scanning calorimetry. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011, 8, 447-449.	0.8	6
79	Analytical Model of Stress Relaxation in 3C SiC Layers on Silicon. <i>Materials Science Forum</i> , 2011, 679-680, 79-82.	0.3	3
80	TiAl-Ni ohmic contacts on 3C-SiC doped by nitrogen or phosphorus implantation. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2010, 171, 120-126.	3.5	16
81	Ni based planar Schottky diodes on gallium nitride (GaN) grown on sapphire. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2010, 7, 112-115.	0.8	15
82	Micromachining of thin 3C-SiC films for mechanical properties investigation. <i>Materials Research Society Symposia Proceedings</i> , 2010, 1246, 1.	0.1	14
83	Active Devices for Power Electronics: SiC vs III-N Compounds – The Case of Schottky Rectifiers. <i>Materials Science Forum</i> , 2010, 645-648, 879-884.	0.3	3
84	Evidence of electrical activity of extended defects in 3C-SiC grown on Si. <i>Applied Physics Letters</i> , 2010, 96, .	3.3	65
85	Evaluation of the Crystalline Quality of Strongly Curved 3C-SiC/Si Epiwafers Through X-Ray Diffraction Analyses. , 2010, , .		0
86	High Quality Ohmic Contacts on n-type 3C-SiC Obtained by High and Low Process Temperature. , 2010, , .		10
87	Low Stress Heteroepitaxial 3C-SiC Films Characterized by Microstructure Fabrication and Finite Elements Analysis. <i>Journal of the Electrochemical Society</i> , 2010, 157, H438.	2.9	20
88	Detailed study of the influence of surface misorientation on the density of Anti-Phase Boundaries in 3C-SiC layers grown on (001) silicon. , 2010, , .		6
89	Process Parameters Influence on Specific Contact Resistance (SCR) Value for TiAl Ohmic Contacts on GaN Grown on Sapphire. <i>Materials Science Forum</i> , 2009, 615-617, 955-958.	0.3	9
90	A study of defect evolution in multi-energy helium implanted monocrystalline and polycrystalline silicon. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009, 6, 1964-1968.	0.8	2

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91	Evaluation of Parylene as Protection Layer for Capacitive Micromachined Ultrasonic Transducers. ECS Transactions, 2008, 11, 25-33.	0.5	4
92	Diffusion and Activation of Ultra Shallow Boron Implants in Silicon in Proximity of Voids. Solid State Phenomena, 2008, 131-133, 357-362.	0.3	2
93	Influence of a top layer on cavity formation and helium desorption in silicon. Radiation Measurements, 2008, 43, S583-S587.	1.4	2
94	Strengths and Limitations of the Vacancy Engineering Approach for the Control of Dopant Diffusion and Activation in Silicon. Materials Research Society Symposia Proceedings, 2008, 1070, 1.	0.1	6
95	P Implantation Effect on Specific Contact Resistance in 3C-SiC Grown on Si. Materials Research Society Symposia Proceedings, 2008, 1068, 1.	0.1	2
96	Low Specific Contact Resistance to 3C-SiC Grown on (100) Si Substrates. Materials Science Forum, 2007, 556-557, 721-724.	0.3	8
97	Protection Layer Influence on Capacitive Micromachined Ultrasonic Transducers Performance. Materials Research Society Symposia Proceedings, 2007, 1052, 1.	0.1	2
98	Ultra deep trench doping in silicon by grazing incident boron implantation. Nuclear Instruments & Methods in Physics Research B, 2007, 257, 275-278.	1.4	1
99	Modification of He implantation induced defects using fluorine co-implantation. Nuclear Instruments & Methods in Physics Research B, 2007, 257, 240-243.	1.4	2
100	Effect of voids-controlled vacancy supersaturations on B diffusion. Nuclear Instruments & Methods in Physics Research B, 2007, 257, 249-252.	1.4	6
101	Dielectric function of disorder in high-fluence helium-implanted silicon. Nuclear Instruments & Methods in Physics Research B, 2006, 253, 192-195.	1.4	7
102	Boron interaction with extended defects induced by He ⁺ H co-implantation in Si. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2005, 124-125, 266-270.	3.5	4
103	Boron diffusion in presence of defects induced by helium implantation. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2005, 124-125, 271-274.	3.5	5
104	Impact of Hydrogen Implantation on Helium Implantation Induced Defects. Solid State Phenomena, 2005, 108-109, 309-314.	0.3	3
105	Defects Induced by Helium Implantation: Impact on Boron Diffusivity. Materials Research Society Symposia Proceedings, 2005, 864, 741.	0.1	0
106	Enhancement of He-induced cavities in silicon by hydrogen plasma treatment. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2005, 23, 990.	1.6	3
107	Optical models for cavity profiles in high-dose helium-implanted and annealed silicon measured by ellipsometry. Journal of Applied Physics, 2005, 97, 123514.	2.5	9
108	Interaction between dislocations and He-implantation-induced voids in GaN epitaxial layers. Applied Physics Letters, 2005, 86, 211911.	3.3	20

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109	Properties of Cavities Induced by Helium Implantation in Silicon and their Applications to Devices. Solid State Phenomena, 2004, 95-96, 297-306.	0.3	4
110	Dopant Segregation on Cavities Induced by Helium Implantation: Impact of the Doping Level. Solid State Phenomena, 2004, 95-96, 599-606.	0.3	0
111	Doping Effect of Helium Induced Nanocavities in Silicon. Solid State Phenomena, 2004, 95-96, 325-330.	0.3	1
112	Optimization of the fabrication of sealed capacitive transducers using surface micromachining. Journal of Micromechanics and Microengineering, 2004, 14, 299-304.	2.6	17
113	Impact of Hydrogen Plasma Treatment on Gettering by He Implantation-Induced Cavities in Silicon. Materials Research Society Symposia Proceedings, 2004, 813, 421.	0.1	1
114	Depth distribution of disorder and cavities in high dose helium implanted silicon characterized by spectroscopic ellipsometry. Thin Solid Films, 2004, 455-456, 344-348.	1.8	8
115	A simple model for boron trapping by He implantation extended defects in Si: the role of boron diffusivity. Nuclear Instruments & Methods in Physics Research B, 2004, 216, 291-296.	1.4	14
116	Gettering by helium implantation applied to a device: impact of metal and dopant segregation. Microelectronic Engineering, 2003, 66, 496-503.	2.4	2
117	The evolution of cavities in Si co-implanted with Si and He ions ¹ . Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2003, 102, 75-79.	3.5	4
118	Effects of Self-Ion Implantation on the Thermal Growth of He-Induced Cavities in Silicon. Solid State Phenomena, 2003, 95-96, 337-342.	0.3	0
119	Modification of MeV He Implantation-Induced Cavities in Silicon by Hydrogen Plasma Treatment. Solid State Phenomena, 2003, 95-96, 307-312.	0.3	2
120	The role of a top oxide layer in cavities formed by MeV He implantation into Si. EPJ Applied Physics, 2003, 23, 45-48.	0.7	8
121	Impact of gettering by helium implantation on boron and iron segregation. EPJ Applied Physics, 2003, 23, 41-44.	0.7	2
122	Gettering Induced by Helium Implantation: Application to a Device. Solid State Phenomena, 2002, 82-84, 279-284.	0.3	8
123	Gettering on Cavities Induced by Helium Implantation in Si: The Case of Boron. Japanese Journal of Applied Physics, 2002, 41, 3625-3628.	1.5	7
124	Defects Induced by Helium Implantation: Interaction with Boron and Phosphorus. Materials Research Society Symposia Proceedings, 2002, 719, 431.	0.1	2
125	Trapping of aluminium by dislocation loops in Si. Nuclear Instruments & Methods in Physics Research B, 2001, 178, 188-191.	1.4	1
126	Boron gettering on cavities induced by helium implantation in Si. Nuclear Instruments & Methods in Physics Research B, 2001, 183, 318-322.	1.4	13

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127	Dopant Segregation on Cavities Induced by Helium Implantation: The Case of Boron and Phosphorus. Solid State Phenomena, 2001, 82-84, 309-314.	0.3	5
128	Dopant - Extended Defects Interactions: The Case of Aluminum. Materials Research Society Symposia Proceedings, 2000, 610, 641.	0.1	0
129	Transient enhanced diffusion in preamorphized silicon: the role of the surface. Nuclear Instruments & Methods in Physics Research B, 1999, 148, 257-261.	1.4	47
130	Electrically active defects in BF ₂ ⁺ implanted and germanium preamorphized silicon. Nuclear Instruments & Methods in Physics Research B, 1998, 134, 195-201.	1.4	11
131	The effect of the growth procedure and the InAs amount on the formation of strain-induced islands in the InAs/InP(001) system. Applied Surface Science, 1998, 123-124, 751-756.	6.1	12
132	Elastic energy of strained islands: Contribution of the substrate as a function of the island aspect ratio and inter-island distance. Applied Physics Letters, 1998, 72, 2984-2986.	3.3	30
133	Boron Ted in Pre-Amorphised Si: Role of the A/C Interface. Materials Research Society Symposia Proceedings, 1998, 532, 55.	0.1	2
134	On the «A Symmetrical» Behavior of Transient Enhanced Diffusion in Pre-Amorphised Si Wafers. Materials Research Society Symposia Proceedings, 1998, 532, 67.	0.1	9
135	Electrical Active Defects in the Band-Gap Induced by Ge-Preamorphization of Si-Substrates. Materials Research Society Symposia Proceedings, 1998, 532, 85.	0.1	0
136	Electronic Defect Levels in Ultra-Shallow p+n Junctions Formed by Low-Energy B Ion Implantation into Ge-Preamorphized Silicon. Japanese Journal of Applied Physics, 1997, 36, 4346-4350.	1.5	7
137	Influence of Depth Position of End-of-Range Defects on Current-Voltage and Noise Characteristics of Shallow (p+/n) Junctions. Japanese Journal of Applied Physics, 1997, 36, 1999-2003.	1.5	5
138	Transient enhanced diffusion of boron in presence of end-of-range defects. Journal of Applied Physics, 1997, 82, 2855-2861.	2.5	47
139	The effect of the boron doping level on the thermal behavior of end-of-range defects in silicon. Applied Physics Letters, 1997, 71, 365-367.	3.3	33
140	Electrical Defects of Shallow (P+/N) Junctions Formed by Boron Implantation into Ge-Preamorphized Si-Substrates. Materials Research Society Symposia Proceedings, 1997, 469, 413.	0.1	1
141	Interactions between Dopants and End-of-Range Defects in Silicon. Solid State Phenomena, 1996, 47-48, 195-204.	0.3	23
142	Transient Enhanced Diffusion of Dopants in Preamorphised Si Layers. Materials Research Society Symposia Proceedings, 1996, 438, 3.	0.1	10
143	TED of boron in the presence of EOR defects: the use of the theory of Ostwald ripening to calculate Si-interstitial supersaturation in the vicinity of extrinsic defects. Nuclear Instruments & Methods in Physics Research B, 1996, 112, 129-132.	1.4	5
144	Is there an effect of the proximity of a «free-surface» on the formation of End-Of-Range defects?. Nuclear Instruments & Methods in Physics Research B, 1996, 120, 5-8.	1.4	28

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145	Residual Stress Measurement and Simulation of 3C-SiC Single and Poly Crystal Cantilevers. Materials Science Forum, 0, 645-648, 865-868.	0.3	4
146	Electrical Characterization of Nitrogen Implanted 3C-SiC by SSRM and CÂTLM Measurements. Materials Science Forum, 0, 679-680, 193-196.	0.3	6
147	Si<sup>+</sup>+</sup>; Implantation and Activation in GaN Comparison of GaN on Sapphire and GaN on Silicon. Materials Science Forum, 0, 711, 213-217.	0.3	3
148	Dose Influence on Physical and Electrical Properties of Nitrogen Implantation in 3C-SiC on Si. Materials Science Forum, 0, 711, 154-158.	0.3	4
149	Elaboration of Monocrystalline Si Thin Film on 3C-SiC(100)/Si Epilayers by Low Pressure Chemical Vapor Deposition. Materials Science Forum, 0, 711, 61-65.	0.3	7
150	ICP Etching of 4H-SiC Substrates. Materials Science Forum, 0, 740-742, 825-828.	0.3	5
151	Aluminum Implantation in 4H-SiC: Physical and Electrical Properties. Materials Science Forum, 0, 740-742, 581-584.	0.3	3
152	3C-SiC: New Interest for MEMS Devices. Materials Science Forum, 0, 806, 3-9.	0.3	3
153	Silicon Growth on 3C-SiC(001)/Si(001): Pressure Influence and Thermal Effect. Materials Science Forum, 0, 821-823, 978-981.	0.3	5
154	Structural Study of the Innovative 3C-SiC/Si/3C-SiC/Si Heterostructure for Electro-Mechanical Applications. Materials Science Forum, 0, 858, 143-146.	0.3	2
155	Influence of Aluminum Incorporation on Mechanical Properties of 3C-SiC Epilayers. Materials Science Forum, 0, 924, 318-321.	0.3	3
156	Laser Annealing Simulations of Metallisations Deposited on 4H-SiC. Materials Science Forum, 0, 963, 502-505.	0.3	4
157	Optimisation of Ti Ohmic Contacts Formed by Laser Annealing on 4H-SiC. Materials Science Forum, 0, 1062, 219-223.	0.3	2
158	Designing SiC Based CMUT Structures: An Original Approach and Related Material Issues. Materials Science Forum, 0, 1062, 94-98.	0.3	2